32K x 16 Static RAM

Features

- 5.0V operation (± 10%)
- · High speed
 - t_{AA} = 10 ns
- Low active power
 - 825 mW (max., 10 ns, "L" version)
- · Very Low standby power
 - 550 μW (max., "L" version)
- Automatic power-down when deselected
- Independent Control of Upper and Lower bytes
- Available in 44-pin TSOP II and 400-mil SOJ

Functional Description

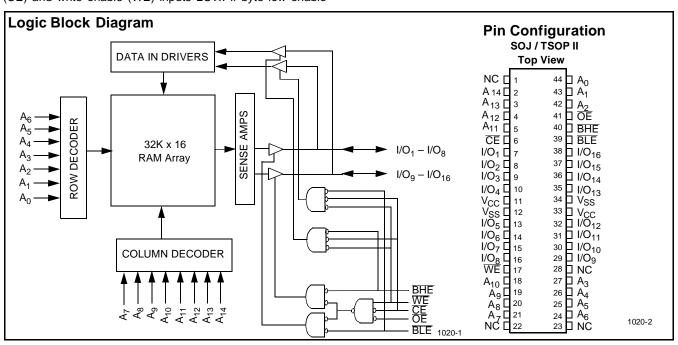
The CY7C1020 is a high-performance CMOS static RAM organized as 32,768 words by 16 bits. This device has an automatic power-down feature that significantly reduces power consumption when deselected.

Writing to the device is accomplished by taking chip enable (CE) and write enable (WE) inputs LOW. If byte low enable (BLE) is LOW, then data from I/O pins (I/O₁ through I/O₈), is written into the location specified on the address pins (An through A₁₄). If byte high enable (BHE) is LOW, then data from I/O pins (I/O_9 through I/O_{16}) is written into the location specified on the address pins (A_0 through A_{14}).

Reading from the device is accomplished by taking chip enable (CE) and output enable (OE) LOW while forcing the write enable (WE) HIGH. If byte low enable (BLE) is LOW, then data from the memory location specified by the address pins will appear on I/O₁ to I/O₈. If byte high enable (BHE) is LOW, then data from memory will appear on I/O₉ to I/O₁₆. See the truth table at the back of this datasheet for a complete description of read and write modes.

The input/output pins (I/O₁ through I/O₁₆) are placed in a high-impedance state when the device is deselected (CE HIGH), the outputs are disabled (OE HIGH), the BHE and BLE are disabled (BHE, BLE HIGH), or during a write operation (CE LOW, and \overline{WE} LOW).

The CY7C1020 is available in standard 44-pin TSOP type II and 400-mil-wide SOJ packages.



Selection Guide

		7C1020-10	7C1020-12	7C1020-15	7C1020-20
Maximum Access Time (ns)		10	12	15	20
Maximum Operating Current (mA)		180	170	160	160
	L	150	140	130	130
Maximum CMOS Standby Current (mA)		3	3	3	3
	L	0.1	0.1	0.1	0.1

Shaded area contains advance information.



Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.) Storage Temperature-65°C to +150°C Ambient Temperature with Power Applied–55°C to +125°C Supply Voltage on V_{CC} to Relative $GND^{[1]}$ -0.5V to +7.0VDC Voltage Applied to Outputs in High Z State^[1].....-0.5V to V_{CC} +0.5V DC Input Voltage^[1].....-0.5V to V_{CC} +0.5V

Current into Outputs (LOW)	20 mA
Static Discharge Voltage(per MIL-STD-883, Method 3015)	>2001V
Latch-Up Current	>200 mA

Operating Range

Range	Ambient Temperature ^[2]	v _{cc}
Commercial	0°C to +70°C	4.5V-5.5V

Electrical Characteristics Over the Operating Range

				7C10	7C1020-10		7C1020-12		7C1020-15	
Parameter	Description	Test Conditions		Min.	Max.	Min.	Max.	Min.	Max.	Unit
V _{OH}	Output HIGH Voltage	$V_{CC} = Min., I_{OH} = -4.0$	$V_{CC} = Min., I_{OH} = -4.0 \text{ mA}$			2.4		2.4		V
V _{OL}	Output LOW Voltage	V _{CC} = Min., I _{OL} = 8.0 m	A		0.4		0.4		0.4	V
V _{IH}	Input HIGH Voltage			2.2	6.0	2.2	6.0	2.2	6.0	V
V _{IL}	Input LOW Voltage ^[1]			-0.5	0.8	-0.5	8.0	-0.5	0.8	V
I _{IX}	Input Load Current	$GND \le V_1 \le V_{CC}$		-1	+1	-1	+1	-1	+1	μΑ
I _{OZ}	Output Leakage Current	$GND \leq V_I \leq V_CC,$ Output Disabled		-2	+2	-2	+2	-2	+2	μА
I _{CC}	V _{CC} Operating	V _{CC} = Max.,			180		170		160	mA
	Supply Current	$I_{OUT} = 0 \text{ mÅ},$ $f = f_{MAX} = 1/t_{RC}$	L		150		140		130	
I _{SB1}	Automatic CE	Max. V _{CC} , CE ≥ V _{IH}			20		20		20	mA
	Power-Down Current —TTL Inputs	$V_{IN} \ge V_{IH}$ or $V_{IN} \le V_{IL}$, $f = f_{MAX}$	L		10		10		10	
I _{SB2}	Automatic CE	Max. V _{CC} ,			3		3		3	mA
	Power-Down Current —CMOS Inputs	$CE \ge V_{CC} - 0.3V,$ $V_{IN} \ge V_{CC} - 0.3V,$ or $V_{IN} \le 0.3V,$ f=0			100		100		100	μА

Shaded area contains advance information.

V_{IL} (min.) = -2.0V for pulse durations of less than 20 ns.
 T_A is the "instant on" case temperature.



Electrical Characteristics Over the Operating Range (continued)

				7C10	20-20	
Parameter	Description Test Conditions				Max.	Unit
V _{OH}	Output HIGH Voltage	$V_{CC} = Min., I_{OH} = -4.0 \text{ mA}$		2.4		V
V _{OL}	Output LOW Voltage	V _{CC} = Min., I _{OL} = 8.0 mA	V _{CC} = Min., I _{OL} = 8.0 mA		0.4	V
V _{IH}	Input HIGH Voltage			2.2	6.0	V
V _{IL}	Input LOW Voltage ^[1]			-0.5	0.8	V
I _{IX}	Input Load Current	$GND \le V_I \le V_{CC}$		-1	+1	μΑ
I _{OZ}	Output Leakage Current	$GND \le V_1 \le V_{CC}$, Output Dis	$GND \le V_1 \le V_{CC}$, Output Disabled		+2	μΑ
I _{CC}	V _{CC} Operating	V _{CC} = Max.,			160	mA
	Supply Current	$I_{OUT} = 0 \text{ mÅ},$ $f = f_{MAX} = 1/t_{RC}$	L		130	
I _{SB1}	Automatic CE	Max. V _{CC} , CE ≥ V _{IH}			20	mA
	Power-Down Current —TTL Inputs	$V_{IN} \ge V_{IH}$ or $V_{IN} \le V_{IL}$, $f = f_{MAX}$	L		10	
I _{SB2}	Automatic CE	Max. V _{CC} ,			3	mA
	Power-Down Current —CMOS Inputs	$\overline{CE} \ge V_{CC} - 0.3V$, $V_{IN} \ge V_{CC} - 0.3V$, or $V_{IN} \le 0.3V$, f=0	L		100	μА

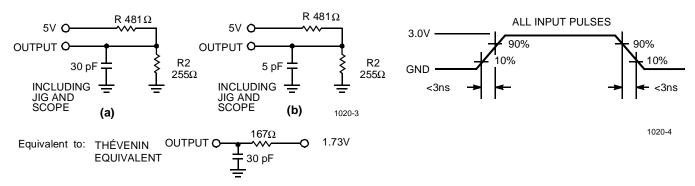
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Capacitance^[3]

Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	$T_A = 25^{\circ}C, f = 1 \text{ MHz},$	8	pF
C _{OUT}	Output Capacitance	$V_{CC} = 5.0V$	8	pF

Note:

AC Test Loads and Waveforms



^{3.} Tested initially and after any design or process changes that may affect these parameters.



PRELIMINARY

Switching Characteristics^[4] Over the Operating Range

		7C10	20-10	7C1020-12		7C1020-15		7C1020-20		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYC	LE	<u>'</u>		•	•		•		•	•
t _{RC}	Read Cycle Time	10		12		15		20		ns
t _{AA}	Address to Data Valid		10		12		15		20	ns
t _{OHA}	Data Hold from Address Change	3		3		3		3		ns
t _{ACE}	CE LOW to Data Valid		10		12		15		20	ns
t _{DOE}	OE LOW to Data Valid		5		5		7		9	ns
t _{LZOE}	OE LOW to Low Z	0		0		0		0		ns
t _{HZOE}	OE HIGH to High Z ^[5, 6]		5		6		7		8	ns
t _{LZCE}	CE LOW to Low Z ^[6]	3		3		3		3		ns
t _{HZCE}	CE HIGH to High Z ^[5, 6]		5		6		7		8	ns
t _{PU}	CE LOW to Power-Up	0		0		0		0		ns
t _{PD}	CE HIGH to Power-Down		12		12		15		20	ns
t _{DBE}	Byte enable to Data Valid		5		6		7		9	ns
t _{LZBE}	Byte enable to Low Z	0		0		0		0		ns
t _{HZBE}	Byte disable to High Z		5		6		7		9	ns
WRITE CYC	:LE ^[7]									
t _{WC}	Write Cycle Time	10		12		15		12		ns
t _{SCE}	CE LOW to Write End	8		9		10		12		ns
t _{AW}	Address Set-Up to Write End	7		8		10		12		ns
t _{HA}	Address Hold from Write End	0		0		0		0		ns
t _{SA}	Address Set-Up to Write Start	0		0		0		0		ns
t _{PWE}	WE Pulse Width	7		8		10		12		ns
t _{SD}	Data Set-Up to Write End	5		6		10		10		ns
t _{HD}	Data Hold from Write End	0		0		0		0		ns
t _{LZWE}	WE HIGH to Low Z ^[6]	3		3		3		3		ns
t _{HZWE}	WE LOW to High Z ^[5, 6]		5		6		7		9	ns
t _{BW}	Byte enable to end of write	7		8		9		12		ns

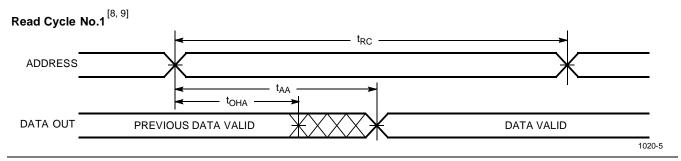
Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified $I_{OL}I_{OH}$ and 30-pF load capacitance.

thzoe, thzee, thzee, thzee, thzee and thzwe are specified with a load capacitance of 5 pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady-state voltage. At any given temperature and voltage condition, thzee is less than thzee, thzee is less than thzee is less than thzee is less than thzee for any given device.

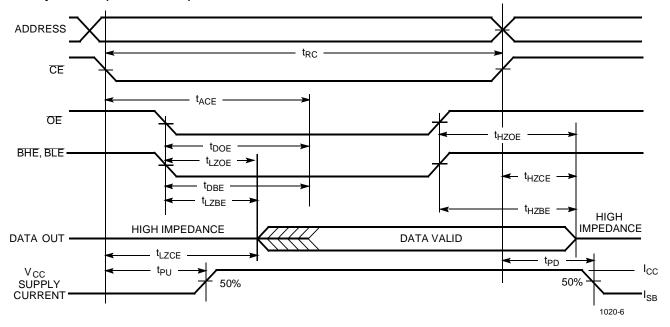
The internal write time of the memory is defined by the overlap of CE LOW, WE LOW and BHE / BLE LOW. CE, WE and BHE / BLE must be LOW to initiate a write, and the transition of these signals can terminate the write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the write.



Switching Waveforms



Read Cycle No.2 ($\overline{\text{OE}}$ Controlled) $^{[9, 10]}$

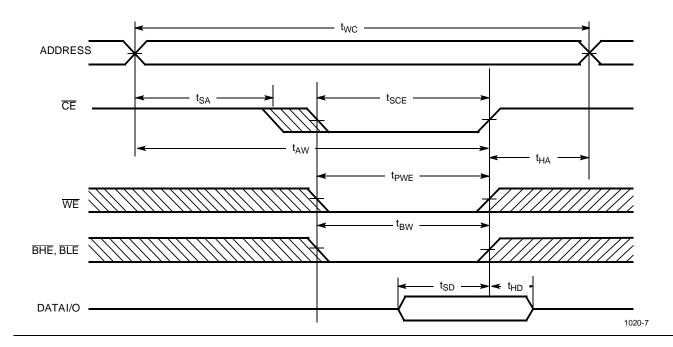


- 8. Device is continuously selected. \overline{OE} , \overline{CE} , \overline{BHE} and/or $\overline{BHE} = V_{IL}$
- 9. WE is HIGH for read cycle.
 10. Address valid prior to or coincident with CE transition LOW.

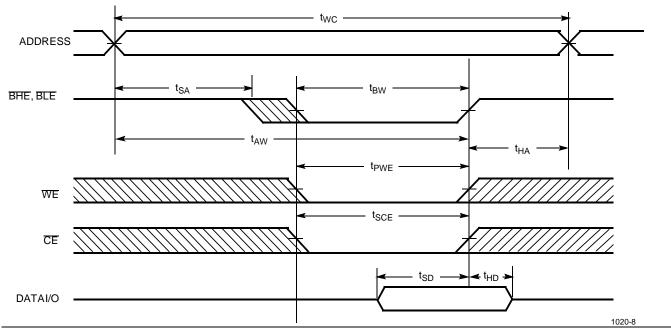


Switching Waveforms (continued)

Write Cycle No. 1 ($\overline{\text{CE}}$ Controlled) [11, 12]



Write Cycle No. 2 (BLE or BHE Controlled)

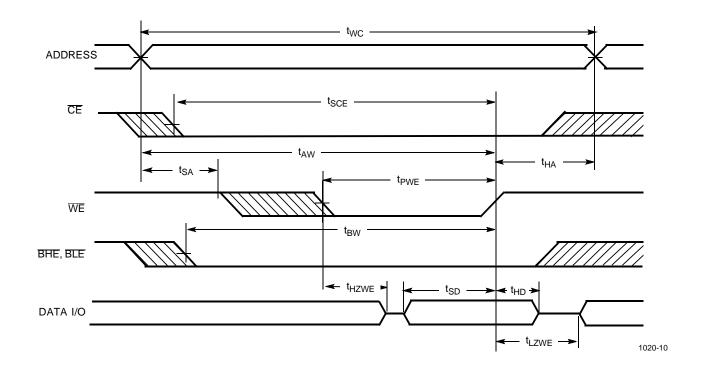


- 11. Data I/O is high impedance if OE or BHE and/or BLE= V_{IH}.
 12. If CE goes HIGH simultaneously with WE going HIGH, the output remains in a high-impedance state.



Switching Waveforms (continued)

Write Cycle No.3 (WE Controlled, OE LOW)



Truth Table

CE	OE	WE	BLE	BHE	I/O ₁ –I/O ₈	I/O ₉ -I/O ₁₆	Mode	Power
Н	Х	Х	Х	Χ	High Z	High Z	Power-Down	Standby (I _{SB})
L	L	Н	L	L	Data Out	Data Out	Read - All bits	Active (I _{CC})
			L	Н	Data Out	High Z	Read - Lower bits only	Active (I _{CC})
			Н	L	High Z	Data Out	Read - Upper bits only	Active (I _{CC})
L	Х	L	L	L	Data In	Data In	Write - All bits	Active (I _{CC})
			L	Н	Data In	High Z	Write - Lower bits only	Active (I _{CC})
			Н	L	High Z	Data In	Write - Upper bits only	Active (I _{CC})
L	Н	Н	Х	Х	High Z	High Z	Selected, Outputs Disabled	Active (I _{CC})
L	Х	Х	Н	Н	High Z	High Z	Selected, Outputs Disabled	Active (I _{CC})



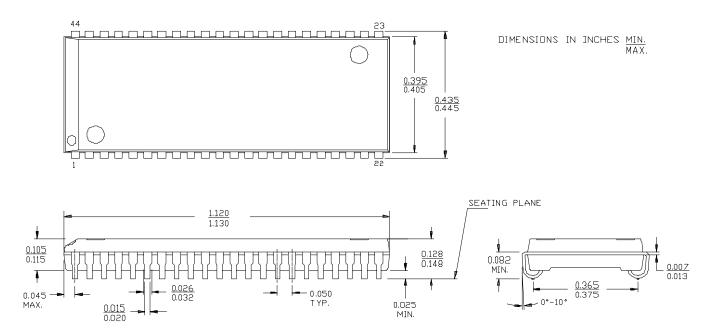
Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
10	CY7C1020-10VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1020L-10VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1020-10ZC	Z44	44-Lead TSOP Type II	Commercial
	CY7C1020L-10ZC	Z44	44-Lead TSOP Type II	Commercial
12	CY7C1020-12VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1020L-12VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1020-12ZC	Z44	44-Lead TSOP Type II	Commercial
	CY7C1020L-12ZC	Z44	44-Lead TSOP Type II	Commercial
15	CY7C1020-15VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1020L-15VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1020-15ZC	Z44	44-Lead TSOP Type II	Commercial
	CY7C1020L-15ZC	Z44	44-Lead TSOP Type II	Commercial
20	CY7C1020-20VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1020L-20VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1020-20ZC	Z44	44-Lead TSOP Type II	Commercial
	CY7C1020L-20ZC	Z44	44-Lead TSOP Type II	Commercial

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Package Diagrams

44-Lead (400-Mil) Molded SOJ V34

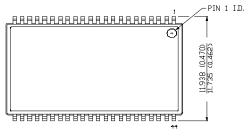


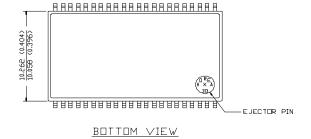


Package Diagrams (continued)

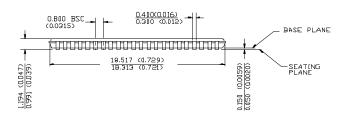
44-Pin TSOP II Z44

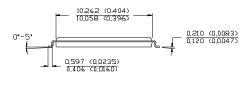
DIMENSION (N MM (INCH)
MAX
MIN
LEAD COPLANARITY 0.004 (NCHES.





TOP VIEW





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